

Day : Sunday  
Date : 06/10/2007

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Time : 01:28:33  
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Docket	Reg-New	Reg. Amend	Spl-New	Spl-Amend	Accl-New	Accl-Amend	Rejected
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**Regular Amended Cases**

(WARNING: Data Security and Confidentiality Restriction Apply)

Name : **SCHILLINGER, LAURA**Examiner Number : **74721**Group Art Unit : **2813**Regular Amended Cases :**52**

Application #	Fwd-to-Exmr	Status	Loc	ChgTo Loc	Class	SubClass	Mo-Old	Unavail	Type	Gau	Title
<u>09/942445</u> IFW IMAGE	01/10/2007	121	e	e	438	122.000	2+	-	-		SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF
<u>10/681507</u> IFW IMAGE	02/07/2007	71	e	e	438	381.000	2+	-	-		ELECTRICALLY ISOLATED IN ACTIVE
<u>11/086446</u> IFW IMAGE	02/23/2007	71	e	e	257	079.000	2+	-	-		SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF
<u>10/276306</u> IFW IMAGE	02/24/2007	71	e	e	438	458.000	2+	-	-		EMBRITTLED SUBSTRATE METHOD FOR MAKING SEMICONDUCTOR
<u>10/485046</u> IFW IMAGE	02/25/2007	71	e	e	257	678.000	2+	-	-		VERTICAL INTEGRATION
<u>10/994265</u> IFW IMAGE	02/27/2007	71	e	e	438	149.000	2+	-	-		THIN FILM TRANSISTOR METHOD OF MANUFACTURING THE SAME
<u>10/986936</u> IFW IMAGE	03/03/2007	71	e	e	438	795.000	2+	-	-		LASER AND APPARATUS FOR ANNEALING OF SEMICONDUCTOR THIN FILM THE SAME

<u>10/992596</u> IFW IMAGE	03/06/2007	71	e	e	438	123.000	2+	-	-	METHOD FOR FABRICATING SEMICONDUCTOR DEVICES USING STRAINED BEARING MATERIAL
<u>09/845336</u> IFW IMAGE	03/13/2007	71	e	e	257	079.000	2+	-	-	GROUP III NITRIDE COMPOUND SEMICONDUCTOR LIGHT-EMIITING DEVICE
<u>10/706912</u> IFW IMAGE	03/13/2007	71	e	e	438	048.000	2+	-	-	ELECTRONIC DEVICES AND PRODUCTION METHODS
<u>10/990711</u> IFW IMAGE	03/19/2007	71	e	e	438	527.000	2+	-	-	SYSTEMS AND METHODS FOR INTEGRATING HETEROGENEOUS CIRCUIT DESIGN
<u>10/831617</u> IFW IMAGE	03/20/2007	71	e	e	438	562.000	2+	-	-	PROCESS OF FABRICATING SEMICONDUCTOR DEVICE
<u>11/223069</u> IFW IMAGE	03/20/2007	71	e	e	438	382.000	2+	-	-	ELECTRONIC PROGRAMMABLE POLYSILICON WITH MULTIPLE LEVEL RESISTANCE AND PROGRESSIVE
<u>10/899833</u> IFW IMAGE	03/23/2007	71	e	e	438	123.000	2+	-	-	SEMICONDUCTOR PROCESSING METHODS FOR FORMING INTEGRATED CIRCUITRY
<u>11/204418</u> IFW IMAGE	03/23/2007	71	e	e	438	197.000	2+	-	-	PROCESS FOR ULTRA-THIN SOI DEVICE INCORPORATING SILICON TRENCHES ARTICLE METHOD THEREBY
<u>10/210109</u> IFW IMAGE	03/24/2007	71	e	e	438	158.000	2+	-	-	PHOTOLITHOGRAPHY METHOD FOR FABRICATING FILM

<u>10/612333</u> IFW IMAGE	03/27/2007	71	e	e	438	123.000	2	-	-	SELECTIVE POLYSILIC GROWTH
<u>10/987135</u> IFW IMAGE	03/30/2007	71	e	e	438	028.000	2	-	-	METHODS (PROCESSING SEMICONDUCTOR WAFER BASED HAVING LIGHT EMITTING (LEDs) THE
<u>10/772585</u> IFW IMAGE	04/05/2007	71	e	e	257	363.000	2	-	-	SEMICONDUCTOR DEVICE
<u>10/799626</u> IFW IMAGE	04/13/2007	71	e	e	438	795.000	1+	-	-	LASER IRRADIATION APPARATUS IRRADIATION METHOD, AND METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE
<u>11/001575</u> IFW IMAGE	04/18/2007	71	e	e	438	458.000	1+	-	-	SUBSTRATE ATTACHING
<u>10/755001</u> IFW IMAGE	04/23/2007	71	e	e	438	643.000	1+	-	-	METHODS (FORMING MATERIAL COMPRISING TUNGSTEN NITROGEN METHODS (FORMING CAPACITOR
<u>10/818155</u> IFW IMAGE	04/23/2007	121	e	e	438	197.000	1+	-	-	DISPOSABLE PROCESS FOR EFFECTIVE FABRICATING
<u>11/217033</u> IFW IMAGE	04/23/2007	71	e	e	257	296.000	1+	-	-	SEMICONDUCTOR PROCESSING METHODS (FORMING TRANSISTOR SEMICONDUCTOR PROCESSING METHODS (FORMING RANDOM ACCESS MEMORY C

										AND RELAT INTEGRATI CIRCUITRY
<u>11/031316</u> IFW IMAGE	04/24/2007	71	e	e	438	112.000	1	-	-	METHOD FO FORMING / FLEXIBLE I FOIL SUBST DISPLAY
<u>11/067186</u> IFW IMAGE	04/24/2007	71	e	e	438	123.000	1	-	-	HIGH PERF FET DEVIC METHODS
<u>10/626620</u> IFW IMAGE	04/26/2007	71	e	e	257	314.000	1	-	-	METHOD TO AN OXIDE ALONG GA EDGE, WHEN SPACE FOR BEGINS WITH OXIDE LINE SURROUND STACK
<u>11/003275</u> IFW IMAGE	05/01/2007	77	e	e	438	279.000	1	-	-	METHODS FORMING INTEGRATI CIRCUITRY METHODS FORMING M CIRCUITRY METHODS FORMING F EFFECT TRANSISTO
<u>11/201504</u> IFW IMAGE	05/02/2007	71	e	e	438	143.000	1	-	-	CAPACITOR SEMICONDUCTOR DEVICE HAVING DUAL DIELECTRIC FILM STRUCTURE AND METHOD OF FABRICATING THE SAME
<u>10/973161</u> IFW IMAGE	05/07/2007	71	e	e	438	105.000	1	-	-	METHODS FORMING / CONDUCTIVE DIAMOND STRUCTURE FORMED THROUGH
<u>11/275850</u> IFW	05/08/2007	71	e	e	438	151.000	-1	-	-	SEMICONDUCTOR DEVICE AND METHOD OF

IMAGE										MANUFACTURE THE SAME
<u>09/685698</u> IFW IMAGE	05/10/2007	71	e	e	257	072.000	-1	-	-	EL DISPLAY AND A METHOD OF MANUFACTURING THE SAME
<u>10/194506</u> IFW IMAGE	05/10/2007	71	e	e	438	151.000	-1	-	-	PROCESS FOR ULTRA-THIN SOI DEVICE INCORPORATING SILICON TITANATE THEREBY
<u>11/544358</u> IFW IMAGE	05/10/2007	71	e	e	257	072.000	-1	-	-	EL DISPLAY AND A METHOD OF MANUFACTURING THE SAME
<u>10/472446</u> IFW IMAGE	05/15/2007	71	e	e	438	478.000	-1	-	-	METHOD FOR MANUFACTURING ZNTE COMPOUND SEMICONDUCTOR SINGLE CRYSTAL ZNTE COMPOUND SEMICONDUCTOR SINGLE CRYSTAL AND SEMICONDUCTOR DEVICE
<u>11/057246</u> IFW IMAGE	05/15/2007	71	e	e	438	123.000	-1	-	-	METHOD OF FORMING SILICON NITRIDE FILM METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
<u>11/296164</u> IFW IMAGE	05/15/2007	71	e	e	438	123.000	-1	-	-	APPLICATION OF DIFFERENT ISOLATION FOR LOGIC EMBEDDED
<u>10/999270</u> IFW IMAGE	05/16/2007	71	e	e	438	197.000	-1	-	-	PHOSPHOR FREE PROCESS POLYSILICON DEFINITION
										METHODS OF FORMING FIELD EFFECT

<u>11/000809</u> IFW IMAGE	05/16/2007	71	e	e	438	300.000	-1	-	-	TRANSISTOR METHODS OF FORMING FIELD EFFECT TRANSISTORS GATES AND LINES
<u>11/377054</u> IFW IMAGE	05/17/2007	71	e	e	438	597.000	-1	-	-	SEMICONDUCTOR CONSTRUCTION
<u>10/419076</u> IFW IMAGE	05/23/2007	71	e	e	438	424.000	-1	-	-	METHOD OF PLANARIZING SURFACE OF SEMICONDUCTOR DEVICE AND SEMICONDUCTOR DEVICE MANUFACTURED ACCORDING TO SAME
<u>10/982115</u> IFW IMAGE	05/24/2007	71	e	e	438	197.000	-1	-	-	ADVANCED DISPOSABLE PROCESS BY TEMPERATURE STRESS IN FILM FOR CMOS TECHNOLOGY
<u>10/019407</u> IFW IMAGE	05/25/2007	71	e	e	438	160.000	-1	-	-	POLYSILICON SEMICONDUCTOR THIN FILM SUBSTRATE METHOD FOR PRODUCING SAME, SEMICONDUCTOR DEVICE, AND ELECTRONIC DEVICE
<u>10/784436</u> IFW IMAGE	06/04/2007	71	e	e	438	106.000	-1	-	-	THROUGH- CONDUCTIVE SEMICONDUCTOR SUBSTRATE METHOD AND SYSTEM FOR MAKING SAME
<u>10/982375</u> IFW	06/04/2007	71	e	e	438	400.000	-1	-	-	METHOD AND MECHANISM STRAINING FOR ENHANCING SPEED OF

IMAGE										INTEGRATI CIRCUITS C DEVICES
<u>11/004836</u> IFW IMAGE	06/04/2007	77	e	e	438	197.000	-1	-	-	SEMICON DEVICE AN METHOD F FABRICATI SAME
<u>11/216915</u> IFW IMAGE	06/05/2007	71	e	e	257	510.000	-1	-	-	SEMICON PROCESSIN METHODS FORMING TRANSISTO SEMICON PROCESSIN METHODS FORMING I RANDOM A MEMORY C AND RELA INTEGRATI CIRCUITRY
<u>10/985666</u> IFW IMAGE	06/06/2007	71	e	e	438	118.000	-1	-	-	SEMICON DEVICE MANUFAC METHOD A MANUFAC APPARATU
<u>10/995406</u> IFW IMAGE	06/07/2007	71	e	e	438	048.000	-1	-	-	METHOD O MANUFAC MEMS DEV
<u>10/996866</u> IFW IMAGE	06/08/2007	71	e	e	438	300.000	-1	-	-	HIGH PERF FET WITH I SOURCE/DI REGION
<u>10/313686</u> IFW IMAGE	06/09/2007	71	e	e	438	105.000	-1	-	-	METHODS FORMING / CONDUCTI DIAMOND STRUCTUR FORMED TI
<u>10/890129</u> IFW IMAGE	06/09/2007	71	e	e	438	123.000	-1	-	-	SEMICON DEVICE AN MANUFAC METHOD

Docket	Reg-New	Reg. Amend	Spl-New	Spl-Amend	Accl-New	Accl-Amend	Rejected
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